TOSHIBA Photocoupler GaAlAs IRed & Photo IC

TLP558

Isolated Bus Driver
High Speed Line Receiver
Microprocessor System Interfaces
MOS FET Gate Driver
Transistor Inverter

The TOSHIBA TLP558 consisits of a GaAlAs light emitting diode and integrated high gain, high speed photodetector.

This unit is 8-lead DIP package.

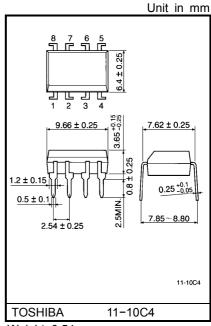
The detector has a three state output stage that provides source drive and sink drive, and built—in schmitt trigger. The detector IC has an internal shield that provides a guaranteed common mode transient immunity of 1000V / μs . TLP558 is inverter logic type. For buffer logic type, TLP555 is in line— μp .

- Input current: IF=1.6mA(max.)
- Power supply voltage: VCC=4.5~20V
- Switching speed: tpHL, tpLH=400ns(max.)
- Common mode transient immunity: ±1000V / µs(min.)
- Guaranteed performance over temperature: -25~85°C
- Isolation voltage: 2500V_{rms}(min.)
- UL recognized: UL1577, file No. E67349

Truth Table(positive logic)

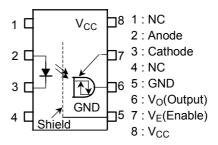
Input	Enable	Output
Н	Н	L
L	Н	Н
Н	L	Z
L	L	Z

A $0.1\mu F$ bypass capacitor must be connected between pins 8 and 5 (see Note 9).

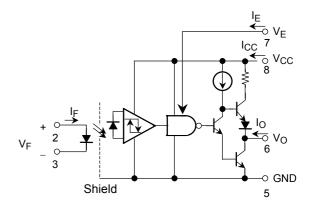


Weight: 0.54 g

Pin Configuration(top view)



Schematic



Maximum Ratings (no derating required up to 85°C unless otherwise noted)

	Charactersitic	Symbol	Rating	Unit	
	Forward current	I _F	10	mA	
LED	Peak transient forward current	(Note 1)	I _{FPT}	1	Α
-	Reverse voltage		V_{R}	5	V
	Output current		IO	40 / –25	mA
	Peak output current	(Note 2)	l _{OP}	80 / -50	mA
ō	Output voltage		Vo	-0.5~20	V
Detector	Supply voltage		V _{CC}	-0.5~20	V
۵	Three state enabel voltage		VE	-0.5~20	V
	Output power dissipation	(Note 3)	PO	100	mW
	Total package power dissipation	(Note 4)	PT	200	mW
Оре	erating temperature range		T _{opr}	−40~85	°C
Sto	rage temperature range	T _{stg}	-55~125	°C	
Lea	d solder temperature(10s)**	T _{sol}	260	°C	
Isol	ation voltage(AC, 1min., R.H.≤ 60%, Ta=25°C)	BVS	2500	Vrms	

⁽Note 1) Pulse width $\leq 1\mu s$, 300pps.

(Note 5) Device considered a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.

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Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Input current, on	I _{F(ON)}	2*	_	5	mA
Input voltage, off	V _{F(OFF)}	0	_	0.8	٧
Supply voltage	V _{CC}	4.5	_	20	٧
Enable voltage high	V _{EH}	2.0	_	20	٧
Enable voltage low	V _{EL}	0	_	0.8	٧
Fan out(TTL load)	N	_	_	4	_
Operating temperature	T _{opr}	-25	_	85	°C

^{*2}mA condition permits at least 20% CTR degradation guardband. Initial switching threshold is 1.6mA or less.

⁽Note 2) Pulse width $\leq 5\mu s$, duty ratio ≤ 0.025 .

⁽Note 3) Derate 1.8mW / °C above 70°C ambient temperature.

⁽Note 4) Derate 3.6mW / °C above 70°C ambient temperature.

^{**1.6}mm below seating plane.

Electrical Characteristics(unless otherwise specified, Ta = -25~85°C, V_{CC} = 4.5~20V)

Characteristic		Symbol	Test Condition			Min.	Тур.*	Max.	Unit	
Input forward voltage		V _F	I _F =5mA, Ta=25°C			_	1.55	1.7	V	
Temperature coefficient of forward voltage		ΔV _F / ΔTa	I _F =5mA			_	-2.0	_	mV / °C	
Input reverse current		I _R	V _R =5V, Ta=25°C	;		_	_	10	μA	
Input capacitance		C _T	V _F =0, f=1MHz, T	a=25°0	0	_	45	_	pF	
Output leakage current			V _F =0,	V _O =V	/ _E =5.5V	_	_	100	^	
$(V_O > V_{CC})$		Гонн	V _{CC} =4.5V	V _O =V	/ _E =20V	_	0.01	500	μA	
Logic low output voltage		V_{OL}	I _{OL} =6.4mA, I _F =1 V _E =2V	.6mA		_	0.4	0.5	٧	
Logic high output voltage		V_{OH}	I _{OH} =-2.6mA, V _F : V _E =2V	-0.8V		2.4	3.3		V	
Logic low enable current		I _{EL}	V _E =0.4V			_	-0.13	-0.32	mA	
			V _E =2.7V			_	_	20		
Logic high enable current		I _{EH}	V _E =5.5V			_	_	100	μΑ	
			V _E =20V			_	0.01	250		
Logic low enable voltage		V _{EL}	_			_	_	0.8	V	
Logic high enable voltage		V_{EH}	_		2.0	_	-	V		
Logic low supply current		ICCL	I _F =5mA	V _{CC} =	:V _E =5.5V	— 4.0		6.0	- mA	
Logic low supply current		ICCL	IF-OIIIA	V _{CC} =	:V _E =20V	_	4.6	7.5	IIIA	
Logic high supply current		Іссн	V _F =0V	V _{CC} =	V _E =5.5V	_	4.2	6.0	mA	
Logic High supply current		ССП	VF 04	V _{CC} =	V _E =20V	_	4.7	7.5	111/1	
		I _{OZL}	V _F =0V V _E =0.8V		V _O =0.4V	_	_	-20		
High impedance state output current	lozh				V _O =2.4V	_	_	20	μΑ	
output ourrent		lozh	I _F =5mA V _E =0.8V		V _O =5.5V	_	_	100		
			1 2 3.31		V _O =20V	_	1	500		
Logic low short circuit		la a.	I _F =5mA	V _O =V	/ _{CC} =5.5V	25	55	_	mΛ	
output current (N	(Note 6)	losL	V _E =2V	V _O =V	/ _{CC} =20V	40	80	_	- mA	
Logic high short circuit	,	laa	V _F =0V, V _O =GND		V _{CC} =5.5V	-10	-25	_	A	
output current (Note 6)		losh	14 014		V _{CC} =20V	-25	-60	_	- mA	
Input current logic low output		I _{FL}	V _E =2V, I _O =6.4mA V _O < 0.4V		_	0.4	1.6	mA		
Input voltage logic high output		V _{FH}	V_E =2V, I_O =-2.6mA V_O > 2.4V			0.8	_	_	٧	

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Electrical Characteristics (unless otherwise specified, $Ta = -25 \sim 85$ °C, $V_{CC} = 4.5 \sim 20$ V)

Characteristic	Symbol	Test Condition	Min.	Typ.*	Max.	Unit
Input current hysteresis	I _{HYS}	V _{CC} =V _E =5V	_	0.05	-	mA
Resistance (input-output)	R _S	V _S =500V, R.H. ≤60% Ta=25°C (Note 5)	5×10 ¹⁰	10 ¹⁴	١	Ω
Capacitance(input–output)	C _S	V _S =0, f=1MHz, Ta=25°C (Note 5)	ı	1.0	ı	pF

^{*}All typical values are at Ta=25°C, V_{CC} =5V, $I_{F(ON)}$ =3mA unless otherwise specified.

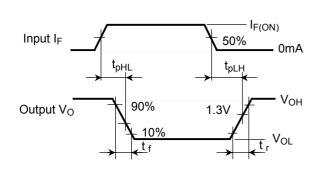
Switching Characteristics(unless otherwise specified, V_{CC} = 4.5~20V, Ta = 25°C)

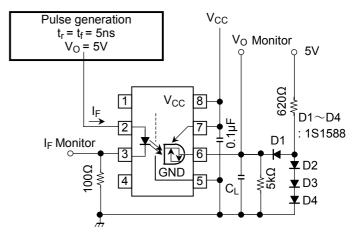
Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Typ.*	Max.	Unit
Propagation delay time to logic high output (No	lote 7)	t _{pLH}		I _F =3→ 0mA	1	250	400	ns
Propagation delay time to logic low output (No	lote 7)	t _{pHL}	1	I _F =0→ 3mA	_	270	400	ns
Output rise time (10-90%)		t _r		$I_F=3\rightarrow 0mA, V_{CC}=5V$		35	75	ns
Output fall time (90–10%)		t _f		$I_F=0 \rightarrow 3mA, V_{CC}=5V$	_	20	75	ns
Output enable time to logic high		t _{pZH}		V _E =0→ 3V	_	_	_	ns
Output enable time to logic low		t _{pZL}	2	V _E =0→ 3V		-		ns
Output disable time from logic high		t _{pHZ}	2	V _E =3→ 0V	_	_	_	ns
Output disable time from logic low		t _{pLZ}		V _E =3→ 0V	_	_	_	ns
Common mode transient immunity at logic high output (No	lote 8)	Смн	3	I _F =0mA, V _{CM} =50V V _{O(Min.)} =2V	1000		_	V / µs
Common mode transient immunity at logic low output (No	lote 8)	C _{ML}	3	I _F =1.6mA, V _{CM} =50V V _{O(Max.)} =0.8V	-1000	_	_	V / µs

^{*} All typical values are at Ta=25 $^{\circ}$ C, V_{CC}=5V

- (Note 6) Duration of output short circuit time should not exceed 10ms.
- (Note 7) The t_{pLH} propagation delay is measured from the 50% point on the trailing edge of the input pulse to the 1.3V point on the leading edge of the output pulse. The t_{pHL} propagation delay is measured from the 50% point on the leading edge of the input pulse to the 1.3V point on the trailing edge of the output pulse.
- (Note 8) C_{ML} is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic low state ($V_O > 0.8V$). C_{MH} is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic state ($V_O > 2.0$).
- (Note 9) A ceramic capacitor (0.1µF) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1cm.

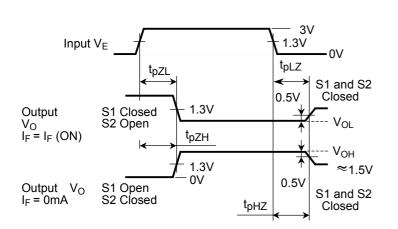
Test Circuit 1: tpLH, tpHL, tr And tf

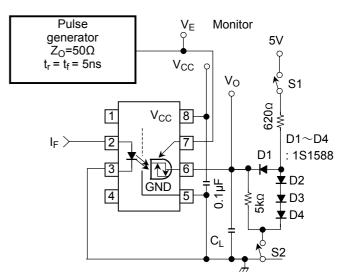




 $\mbox{C}_{\mbox{\scriptsize L}}$ is approximately 15pF which includes probe and stray wiring capacitance.

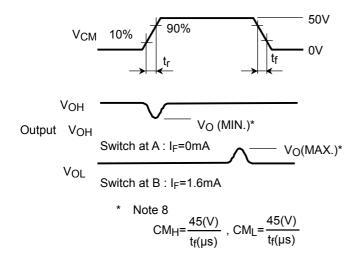
Test Circuit 2: t_{pHZ} , t_{pZH} , t_{pLZ} And t_{pZL}

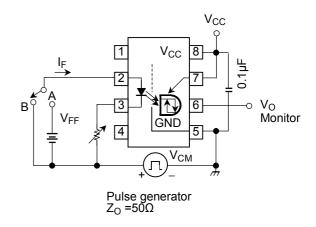




 $\rm C_L$ is approximately $\rm 15_p F$ which includes probe and stray wiring capacitance.

Test Circuit 3: Common Mode Transient Immunity





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